



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} Max | I _D Max T _A = +25°C | | |
|----------------------|--------------------------------|--|--|--|
| -30V | 10mΩ @ V _{GS} = -10V | -11.5A | | |
| | 18mΩ @ V _{GS} = -4.5V | -8.7A | | |

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

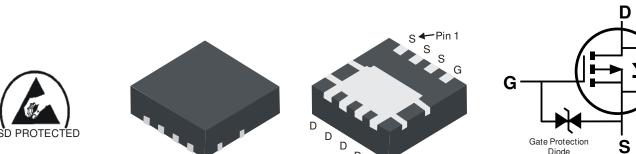
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses Are Minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



POWERDI3333-8

Ordering Information (Note 5)

| Part Number | Case | Packaging |
|----------------|---------------|-------------------|
| DMP3017SFGQ-7 | POWERDI3333-8 | 2,000/Tape & Reel |
| DMP3017SFGQ-13 | POWERDI3333-8 | 3,000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Top View

2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

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Bottom View

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

POWERDI is a registered trademark of Diodes Incorporated.

Equivalent Circuit



Marking Information



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P17= Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 13 = 2013) WW = Week code $(01 \sim 53)$

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|--|-----------------|---|------------------|----------------|-------|
| Drain-Source Voltage | | | V _{DSS} | -30 | V |
| Gate-Source Voltage | | | V _{GSS} | ±25 | V |
| Continuous Drain Current (Noto 7) // 10// | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | ID | -11.5 -9.4 | А |
| Continuous Drain Current (Note 7) $V_{GS} = -10V$ | t<10s | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | ID | -15.2 -12.1 | А |
| Maximum Continuous Body Diode Forward Current (Note 6) | | | Is | -3.0 | А |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | | | I _{DM} | -80 | А |
| Avalanche Current (Note 8) L = 1mH | | | I _{AR} | 14 | А |
| Repetitive Avalanche Energy (Note 8) L = 1mH | | | E _{AR} | 104 | mJ |

Thermal Characteristics

Notes:

| Characteristic | Symbol | Value | Units | | |
|--|----------------------|-----------------------------------|-------------|------|--|
| Total Bower Dissinction (Note 6) | $T_A = +25^{\circ}C$ | D | 0.94 | W | |
| Total Power Dissipation (Note 6) | $T_A = +70^{\circ}C$ | PD | 0.6 | vv | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | D | 137 | °C/W | |
| Thermal Resistance, Junction to Ambient (Note 6) | t<10s | $R_{\theta JA}$ | 82 | °C/W | |
| Total Dower Dissinction (Nate 7) | $T_A = +25^{\circ}C$ | D | 2.2 | W | |
| Total Power Dissipation (Note 7) | $T_A = +70^{\circ}C$ | PD | 1.3 | vv | |
| Thermal Registeres, Junction to Ambient (Note 7) | Steady State | D | 60 | °C/W | |
| Thermal Resistance, Junction to Ambient (Note 7) | t<10s | $R_{\theta JA}$ | 36 | °C/W | |
| Thermal Resistance, Junction to Case (Note 7) | | R _{0JC} | 3.0 | °C/W | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C | |

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout, please see http://www.diodes.com/datasheets/ap02001.pdf for latest version.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$



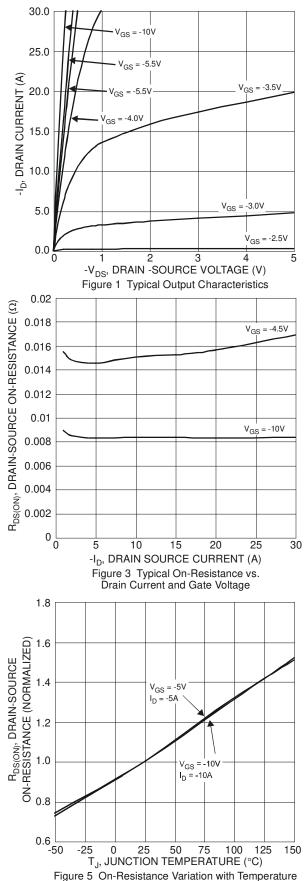
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

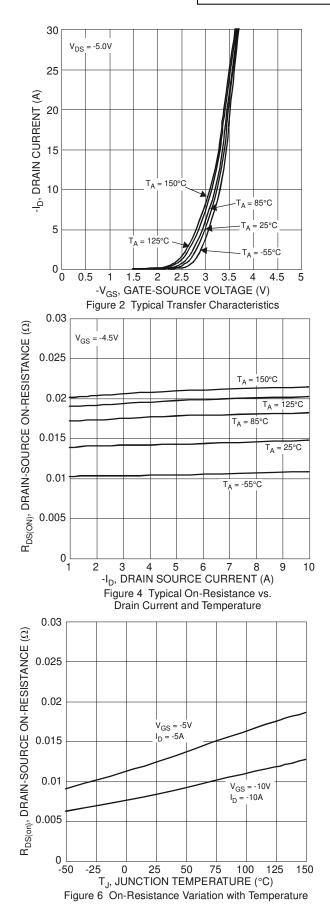
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|---|---------------------|------|------|------|------|--|--|
| OFF CHARACTERISTICS (Note 9) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -30 | | | V | $V_{GS} = 0V, I_D = -250 \mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | -1 | μA | $V_{DS} = -24V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | _ | | ±10 | μA | $V_{GS} = \pm 25V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 9) | <u> </u> | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -1.0 | _ | -3.0 | V | $V_{DS} = V_{GS}, I_D = -250 \mu A$ | |
| Static Drain-Source On-Resistance | P | _ | 8.5 | 10 | mΩ | V _{GS} = -10V, I _D = -11.5A | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 15 | 18 | | $V_{GS} = -4.5V, I_D = -8.5A$ | |
| Forward Transfer Admittance | Y _{fs} | _ | 24 | | S | V _{DS} = -5V, I _D = -11.5A | |
| DYNAMIC CHARACTERISTICS (Note 10) | | | • | • | • | • | |
| Input Capacitance | Ciss | _ | 2246 | _ | pF | | |
| Output Capacitance | Coss | _ | 352 | _ | pF | [−] V _{DS} = -15V, V _{GS} = 0V, − f = 1.0MHz | |
| Reverse Transfer Capacitance | Crss | _ | 294 | | pF | | |
| Gate resistance | Rg | _ | 5.1 | 12 | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ | |
| Total Gate Charge (V _{GS} = 5V) | Qg | _ | 20.5 | _ | nC | | |
| Total Gate Charge (V _{GS} = 10V) | Qg | _ | 41 | | nC | | |
| Gate-Source Charge | Q _{gs} | _ | 7.6 | | nC | V _{DS} = -15V, I _D = -11.5A | |
| Gate-Drain Charge | Q _{gd} | _ | 8.0 | | nC | | |
| Turn-On Delay Time | t _{D(on)} | | 7.5 | | nS | | |
| Turn-On Rise Time | tr | _ | 15.4 | | nS | V _{DD} = -15V, V _{GS} = -10V, | |
| Turn-Off Delay Time | t _{D(off)} | | 45.6 | | nS | $R_{G} = 6\Omega, I_{D} = -11.5A$ | |
| Turn-Off Fall Time | t _f | _ | 36.8 | — | nS | | |
| BODY DIODE CHARACTERISTICS | • | | | | • | 1 | |
| Diode Forward Voltage | V _{SD} | _ | -0.7 | | V | $V_{GS} = 0V, I_{S} = -1A$ | |
| Reverse Recovery Time (Note 9) | t _{rr} | _ | 20 | | nS | | |
| Reverse Recovery Charge (Note 9) | Q _{rr} | _ | 9.5 | _ | nC | - I _S = -11.5A, dl/dt = 100A/μs | |

9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing. Notes:

DMP3017SFGQ

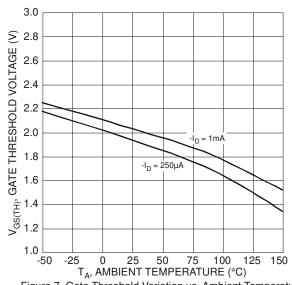


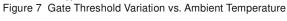


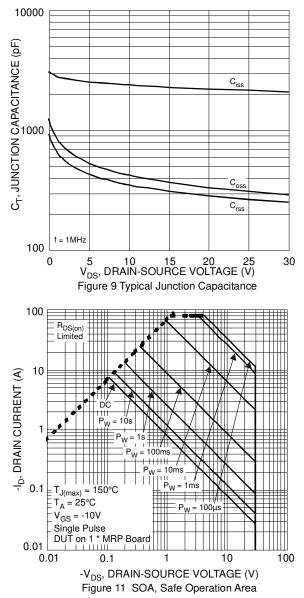


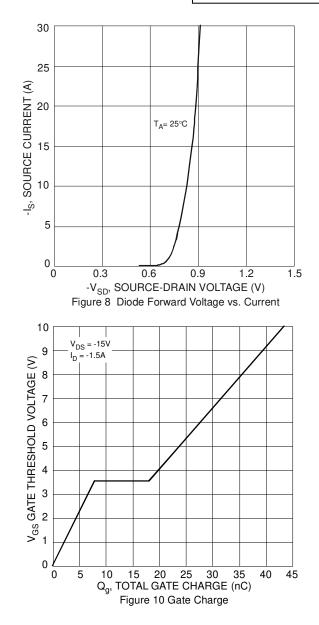
DMP3017SFGQ



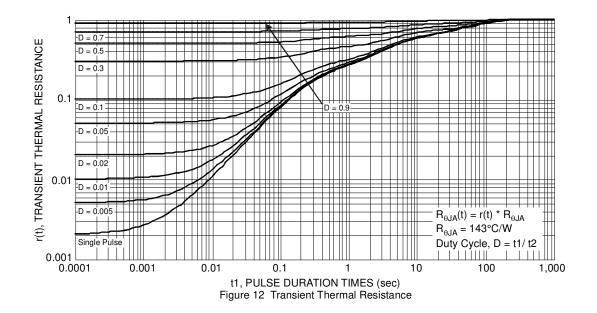








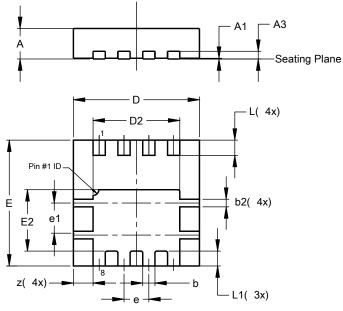






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

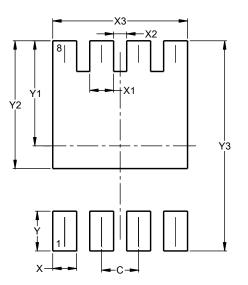


| POWERDI [®] 3333-8 | | | | | | |
|-----------------------------|----------------------|------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.75 | 0.85 | 0.80 | | | |
| A1 | 0.00 | 0.05 | 0.02 | | | |
| A3 | - | - | 0.203 | | | |
| b | 0.27 | 0.37 | 0.32 | | | |
| b2 | _ | - | 0.20 | | | |
| D | 3.25 | 3.35 | 3.30 | | | |
| D2 | 2.22 | 2.32 | 2.27 | | | |
| Е | 3.25 | 3.35 | 3.30 | | | |
| E2 | 1.56 | 1.66 | 1.61 | | | |
| е | - | - | 0.65 | | | |
| e1 | 0.79 | 0.89 | 0.84 | | | |
| L | 0.35 | 0.45 | 0.40 | | | |
| L1 | _ | _ | 0.39 | | | |
| z | _ | _ | 0.515 | | | |
| | All Dimensions in mm | | | | | |

POWERDI3333-8

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



POWERDI3333-8

| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 0.650 | | |
| Х | 0.420 | | |
| X1 | 0.420 | | |
| X2 | 0.230 | | |
| X3 | 2.370 | | |
| Y | 0.700 | | |
| Y1 | 1.850 | | |
| Y2 | 2.250 | | |
| Y3 | 3.700 | | |



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